

RJK2017DPP

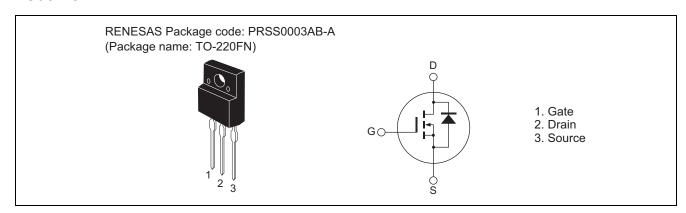
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1797-0200 Rev.2.00 Aug 26, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

			(1u 25 C)
ltem	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D Note4	45	Α
Drain peak current	I _{D (pulse)} Note1	135	Α
Body-drain diode reverse drain current	I _{DR}	45	Α
Avalanche current	I _{AP} Note3	12	Α
Avalanche energy	E _{AR} Note3	9.6	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

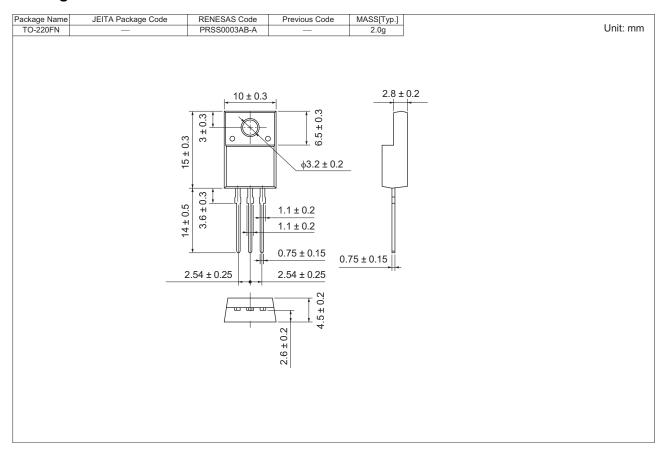
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200	_	_	V	I _D = 10 mA, V _{GS} = 0
Zero gate voltage drain current	I _{DSS}	_	_	1	μА	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2	_	4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	1	0.036	0.047	Ω	$I_D = 22.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	l	4800		pF	V _{DS} = 25 V
Output capacitance	Coss	l	290		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	l	90		pF	
Turn-on delay time	$t_{d(on)}$		50	_	ns	I _D = 22.5 A
Rise time	t _r	_	40	_	ns	V_{GS} = 10 V R_L = 4.5 Ω Rg = 10 Ω
Turn-off delay time	$t_{d(off)}$	_	95	_	ns	
Fall time	t _f	_	40	_	ns	
Total gate charge	Qg	_	66	_	nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	26	_	nC	V _{GS} = 10 V I _D = 45 A
Gate to drain charge	Qgd	_	16	_	nC	
Body-drain diode forward voltage	V_{DF}		0.88	1.35	V	$I_F = 45 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	_	150	_	ns	$I_F = 45 \text{ A}, V_{GS} = 0$ di _F /dt = 100 A/ μ s

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2017DPP-00-T2	1050 pcs	Box (Tube)

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